

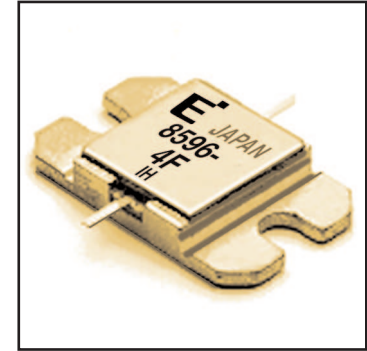
### FEATURES

- High Output Power:  $P_{1dB} = 36.0\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 7.5\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 29\%$  (Typ.)
- Low  $IM_3 = -45\text{dBc}$  @  $P_o = 25.5\text{dBm}$
- Broad Band: 8.5 ~ 9.6GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed

### DESCRIPTION

The FLM8596-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.



### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ\text{C}$	25.0	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of 100 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit	
			Min.	Typ.	Max.		
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	1700	2600	mA	
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 1100\text{mA}$	-	1700	-	mS	
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 85\text{mA}$	-0.5	-1.5	-3.0	V	
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -85\mu\text{A}$	-5.0	-	-	V	
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 8.5 \sim 9.6 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	35.5	36.0	-	dBm	
Power Gain at 1dB G.C.P.	$G_{1dB}$		6.5	7.5	-	dB	
Drain Current	$I_{dsr}$		-	1100	1300	mA	
Power-added Efficiency	$\eta_{add}$		-	29	-	%	
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB	
3rd Order Intermodulation Distortion	$IM_3$		$f = 9.6 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm S.C.L.}$	-42	-45	-	dBc
Thermal Resistance	$R_{th}$		Channel to Case	-	5.0	6.0	$^\circ\text{C/W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$	

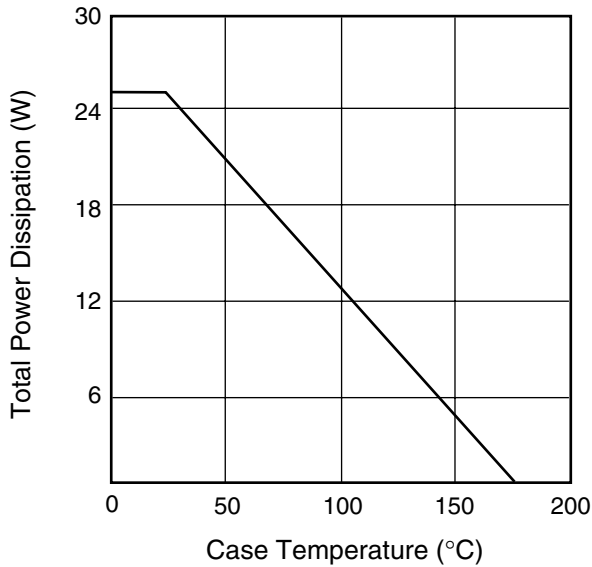
CASE STYLE: IA

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

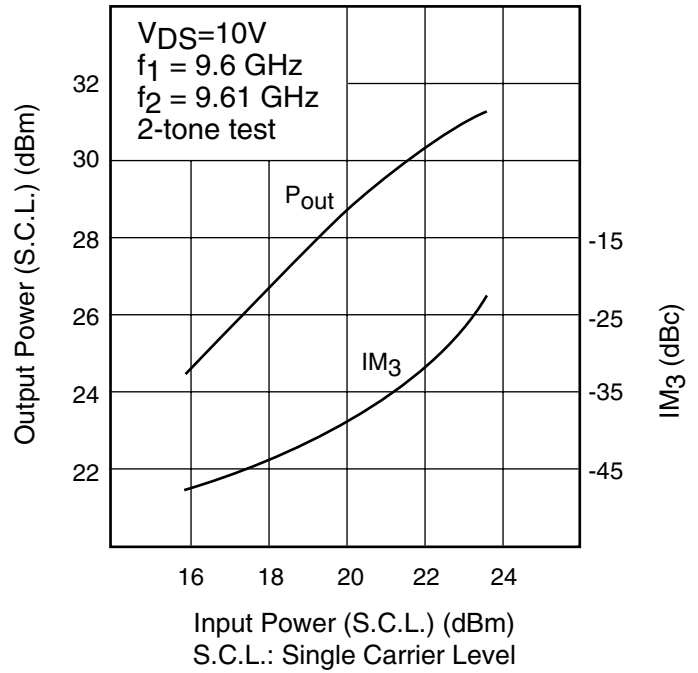
# FLM8596-4F

X, Ku-Band Internally Matched FET

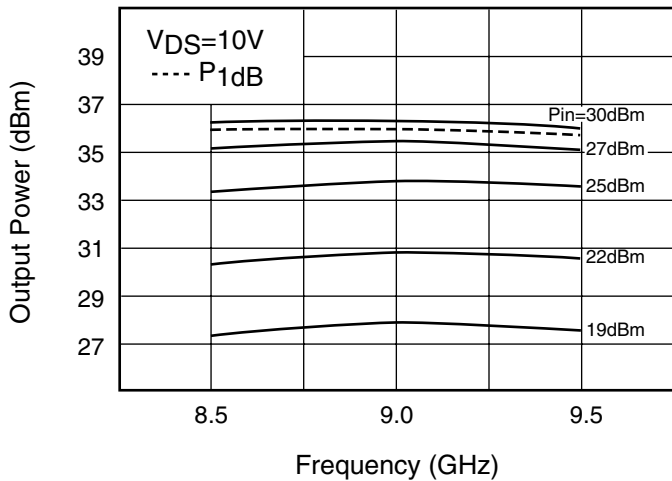
**POWER DERATING CURVE**



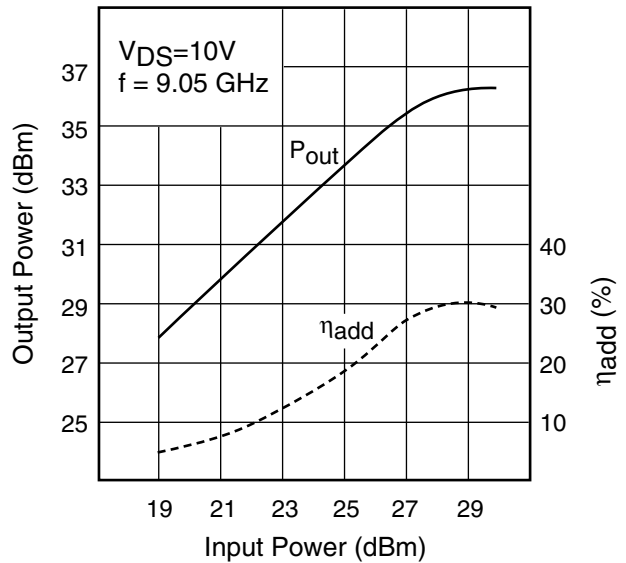
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**



**OUTPUT POWER vs. FREQUENCY**

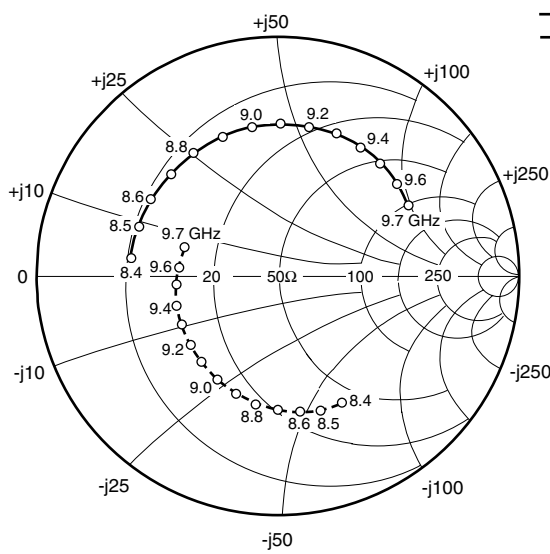


**OUTPUT POWER vs. INPUT POWER**

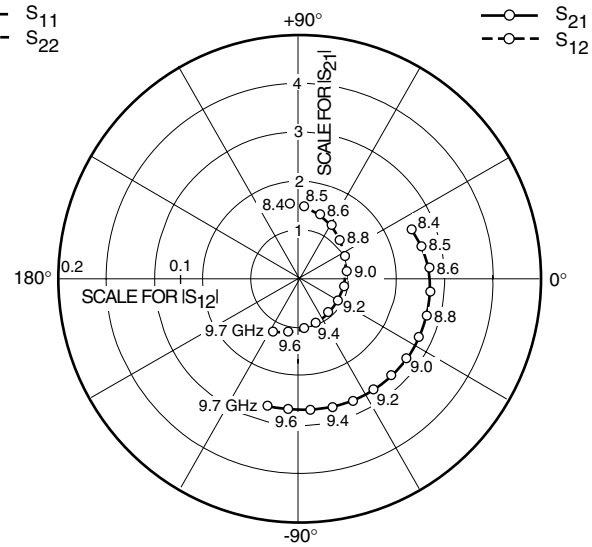


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X, Ku-Band Internally Matched FET



—○— S<sub>11</sub>  
- -○- - S<sub>22</sub>



—○— S<sub>21</sub>  
- -○- - S<sub>12</sub>

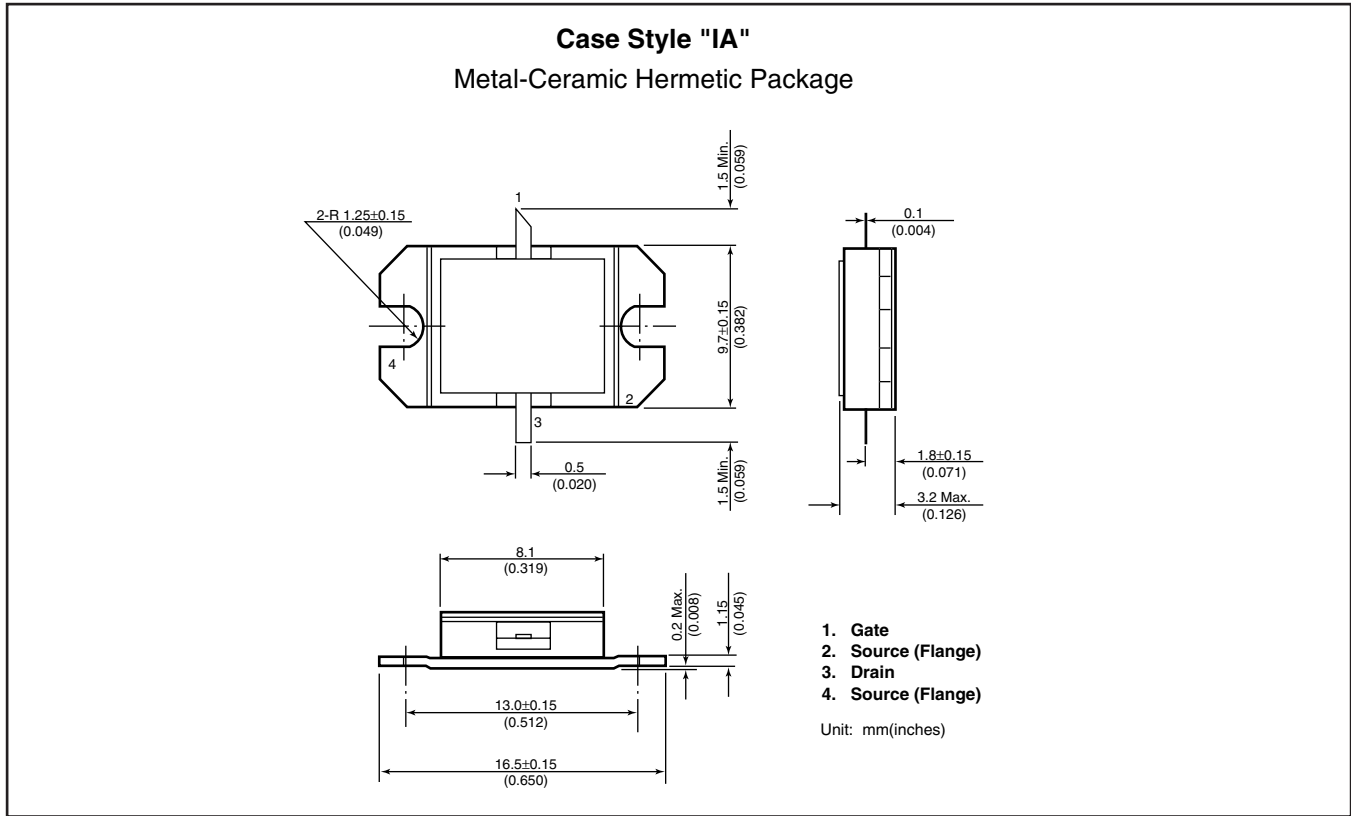
## S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
8400	.623	173.4	2.538	23.8	.062	97.5	.592	-63.5
8500	.620	161.3	2.602	14.2	.059	86.1	.588	-72.3
8600	.622	149.2	2.664	4.4	.056	72.2	.577	-81.1
8700	.622	137.0	2.708	-5.5	.052	58.5	.560	-90.2
8800	.625	124.6	2.748	-15.8	.046	42.4	.548	-99.7
8900	.630	112.4	2.763	-25.9	.042	26.6	.521	-109.8
9000	.632	100.7	2.767	-36.1	.040	10.2	.498	-120.3
9100	.638	89.3	2.764	-46.2	.037	-9.2	.485	-130.2
9200	.637	78.3	2.750	-56.1	.036	-28.0	.465	-141.5
9300	.638	68.0	2.729	-65.8	.037	-49.4	.450	-152.2
9400	.635	57.9	2.718	-75.6	.038	-68.2	.437	-162.7
9500	.631	48.3	2.695	-85.1	.040	-85.7	.420	-174.5
9600	.621	38.5	2.682	-94.8	.044	-103.1	.408	175.8
9700	.611	28.9	2.675	-104.2	.048	-117.1	.401	164.1

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### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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